

MGFK41A4045**14.0-14.5GHz BAND 12.5W INTERNALLY MATCHED GaAs FET****DESCRIPTION**

The MGFK41A4045 is an internally impedance matched GaAs power FET especially designed for use in 14.0-14.5 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

- †Internally impedance matched
- †High output power
P1dB = 41.0dBm(TYP.) @f=14.0-14.5GHz
- †High linear power gain
GLP = 7.0dB(TYP.) @f=14.0-14.5GHz

APPLICATION

For use in 14.0-14.5GHz band amplifiers

QUALITY GRADE

†G

RECOMMENDED BIAS CONDITIONS

VDS = 10 (V)
ID = 3.0 (A)
RG = 50 (ohm)

ABSOLUTE MAXIMUM RATINGS

(Ta=25deg.C)

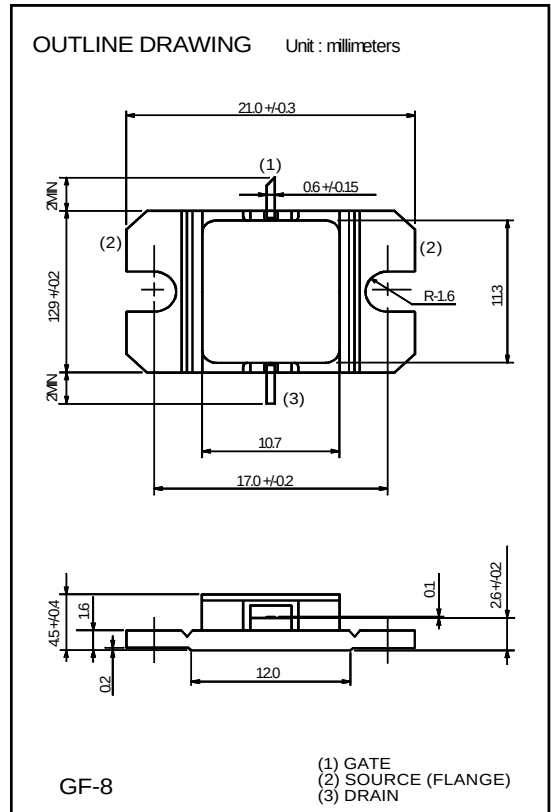
Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain voltage	-15	V
VGSO	Gate to source voltage	-10	V
ID	Drain current	11	A
IGR	Reverse gate current	-36	mA
IGF	Forward gate current	72	mA
PT *1	Total power dissipation	68.2	W
Tch	Channel temperature	175	deg.C
Tstg	Storage temperature	-65 / +175	deg.C

*1 : Tc=25deg.C

ELECTRICAL CHARACTERISTICS

(Ta=25deg.C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS=3V, VG=0V	--	8.0	--	A
gm	Transconductance	VDS=0V, ID=3.0A	--	4	--	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=42mA	-1.0	-1.5	-4.0	V
P1dB	Output power at 1dB gain compression	VDS=10V, ID(RF off)=3.0A, f=14.0 - 14.5GHz	40	41	--	dBm
GLP	Linear power gain		6.0	7.0	--	dB
P.A.E.	Power added efficiency		--	25	--	%
Rth (Ch-C)	Thermal resistance	Channel to Case	--	1.8	2.2	deg.C/W

OUTLINE

< Keep safety first in your circuit designs! >

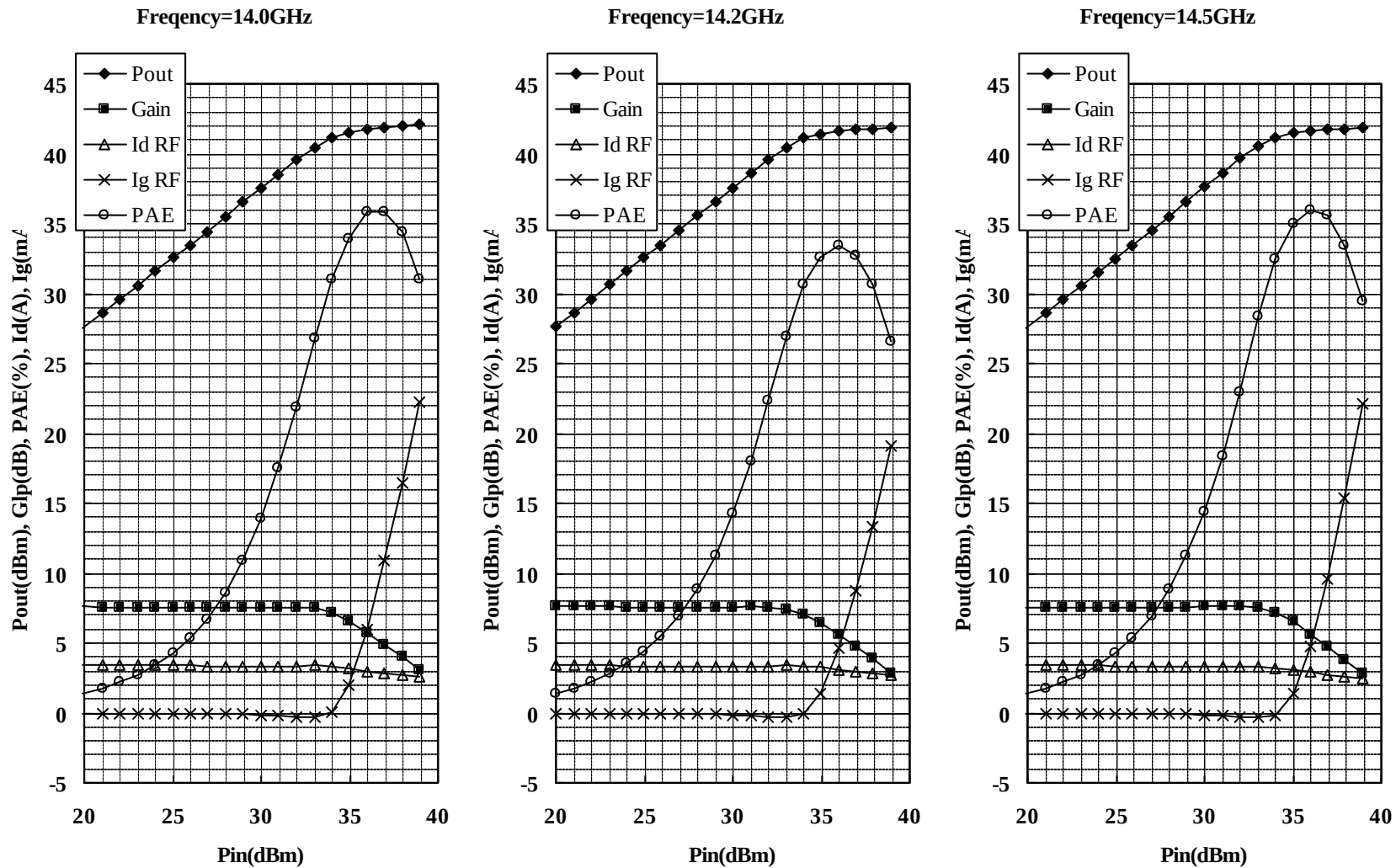
Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (1) placement of substitutive, auxiliary circuits, (2) use of non-flammable material or (3) prevention against any malfunction or mishap.



**MITSUBISHI
ELECTRIC**

MGFK41A4045

OUTPUT POWER & POWER ADDED EFFICIENCY & GAIN vs. INPUT POWER
TEST CONDITIONS : $V_{ds}(R_{f\text{off}})=10\text{V}$, $I_{ds}(R_{f\text{off}})=3.0\text{A}$, $R_g=50\Omega$

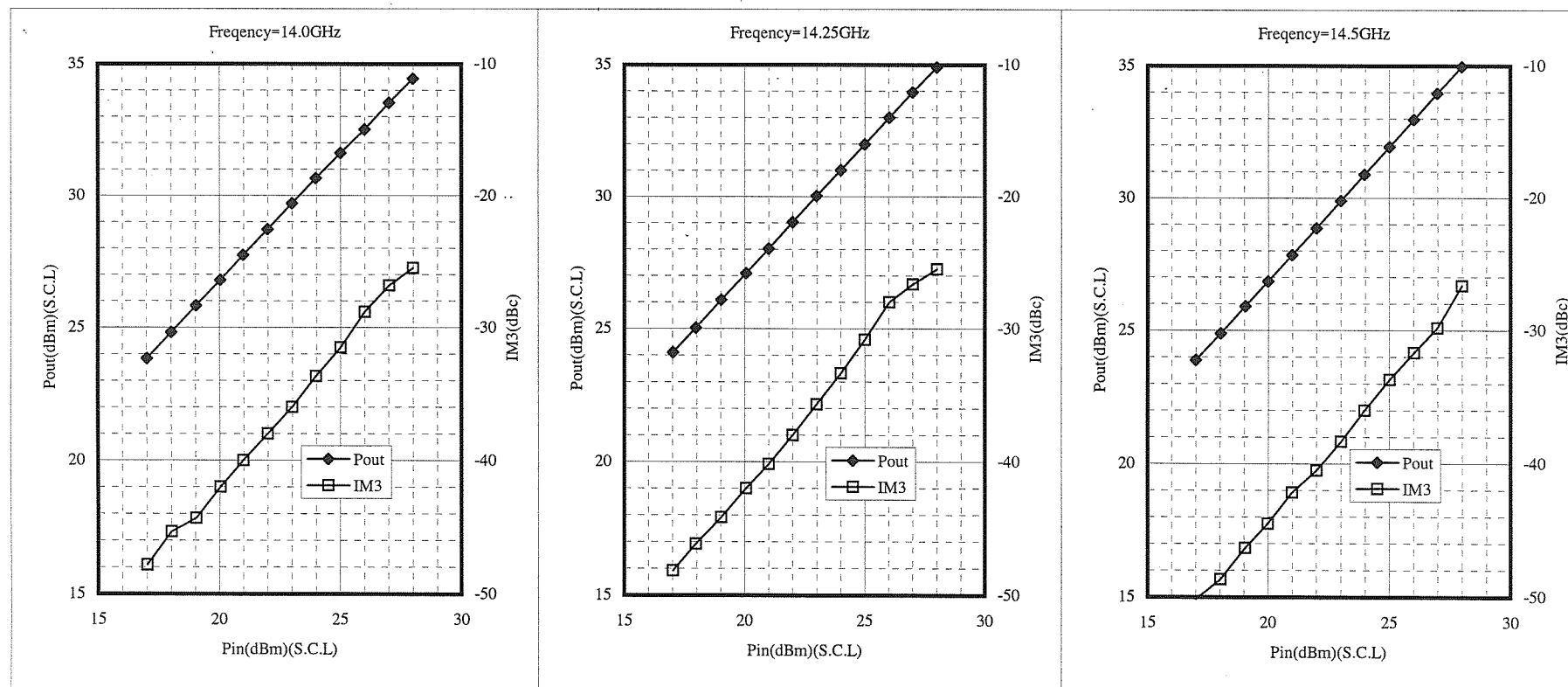


IM3 vs. OUTPUT POWER

TEST CONDITIONS

$V_{ds}(R_{f\text{off}})=10\text{V}$, $I_{ds}(R_{f\text{off}})=3.0\text{A}$, $R_g=50\Omega$

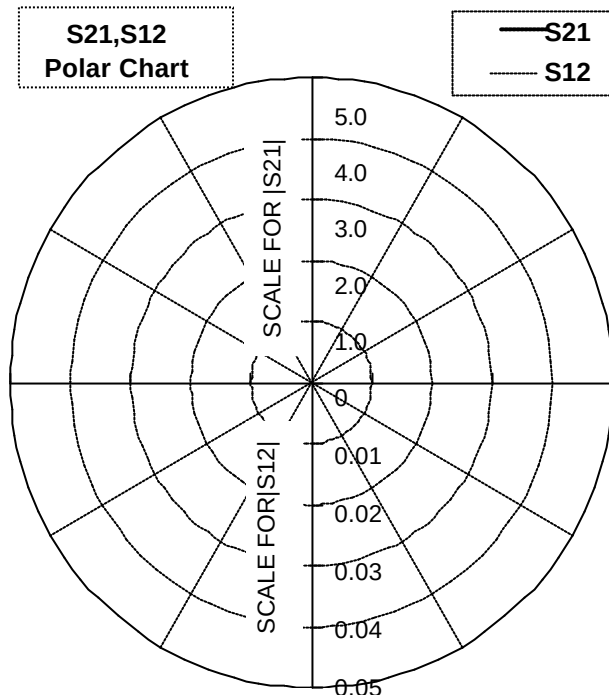
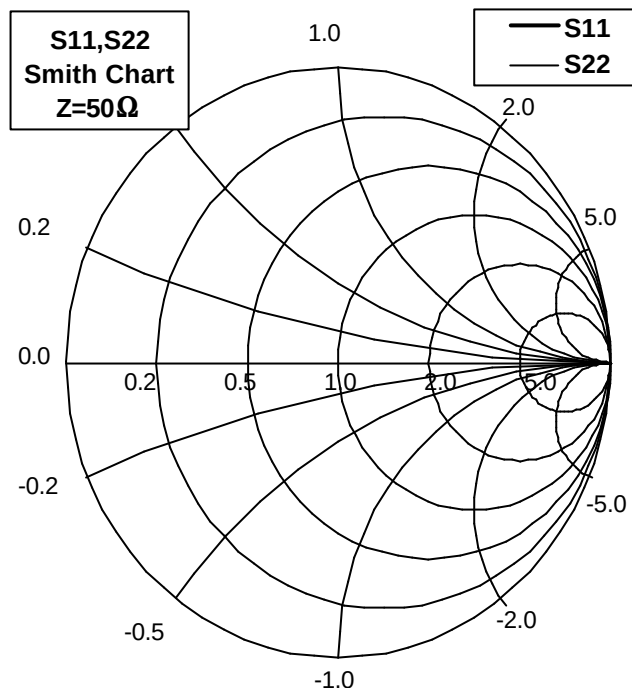
2-tone test, $\Delta f=10\text{MHz}$



MITSUBISHI ELECTRIC CORPORATION

MGFK41A4045

TEST CONDITIONS : f=14.0-14.5GHz,VDS=10V,ID=3.0A



S PARAMETERS (Ta=25deg.C,VDS=10V,ID=3.0A)

f (GHz)	S Parameters (TYP.)							
	S11		S21		S12		S22	
	Mag.	Ang(deg.)	Mag.	Ang(deg.)	Mag.	Ang(deg.)	Mag.	Ang(deg.)
13.00	0.738	-103.4	1.278	34.7	0.057	14.1	0.668	-81.0
13.10	0.716	-109.9	1.349	26.6	0.060	7.6	0.649	-87.3
13.20	0.693	-116.7	1.427	18.2	0.064	0.8	0.628	-93.7
13.30	0.665	-123.8	1.517	9.1	0.068	-6.4	0.609	-101.0
13.40	0.633	-132.2	1.607	-0.1	0.074	-13.6	0.588	-109.0
13.50	0.593	-140.9	1.705	-10.3	0.081	-22.2	0.559	-118.7
13.60	0.546	-151.8	1.809	-23.6	0.087	-33.8	0.521	-131.2
13.70	0.493	-162.0	1.896	-34.7	0.095	-42.9	0.482	-141.7
13.80	0.434	-172.4	1.976	-46.0	0.102	-53.5	0.434	-153.0
13.90	0.369	175.1	2.059	-58.0	0.109	-63.7	0.383	-167.1
14.00	0.303	161.4	2.132	-70.3	0.118	-75.4	0.324	177.1
14.10	0.238	144.2	2.192	-83.2	0.122	-88.5	0.266	159.0
14.20	0.176	120.7	2.241	-96.3	0.127	-100.8	0.215	135.8
14.30	0.118	83.1	2.268	-110.1	0.131	-113.0	0.176	104.0
14.40	0.106	28.9	2.263	-124.6	0.130	-126.2	0.166	64.0
14.50	0.156	-12.7	2.217	-138.9	0.130	-138.3	0.179	28.6
14.60	0.225	-38.3	2.134	-153.0	0.126	-151.4	0.216	0.6
14.70	0.281	-57.4	2.018	-167.1	0.121	-163.3	0.266	-17.8
14.80	0.335	-72.0	1.885	179.9	0.113	-173.9	0.318	-32.7
14.90	0.381	-86.1	1.750	166.9	0.105	176.0	0.353	-46.8
15.00	0.413	-98.3	1.616	154.8	0.098	166.5	0.368	-59.2

MITSUBISHI ELECTRIC CORPORATION